

Title (en)

Method of semiconductor wafer back processing, method of substrate back processing, and radiation-curable pressure-sensitive adhesive sheet

Title (de)

Verfahren zur Bearbeitung der Rückseite eines Halbleiterwafers, Verfahren zur Bearbeitung der Rückseite eines Substrats und strahlungshärtbare druckempfindliche Klebefolie

Title (fr)

Procédé de traitement de la face arrière de plaquettes semi-conductrices, procédé de traitement de la face arrière de substrat, et film adhésif sensible à la pression et durcissable par radiation

Publication

EP 1895581 A3 20120523 (EN)

Application

EP 07016857 A 20070828

Priority

JP 2006232437 A 20060829

Abstract (en)

[origin: EP1895581A2] The present invention relates to a method of semiconductor wafer back processing, which includes applying a radiation-curable pressure-sensitive adhesive sheet comprising a base film and a pressure-sensitive adhesive layer disposed on one side of the base film to a front side of a semiconductor wafer, the front side of the semiconductor wafer having recesses and protrusions; grinding the back side of the semiconductor wafer in such a state that the radiation-curable pressure-sensitive adhesive sheet is adherent to the front side of the semiconductor; and irradiating the pressure-sensitive adhesive sheet with a radiation to thereby cure the pressure-sensitive adhesive layer, followed by subjecting said ground back side of the semiconductor wafer to a surface treatment; and a radiation-curable pressure-sensitive adhesive sheet for use in the method of semiconductor wafer back processing.

IPC 8 full level

H01L 21/68 (2006.01); **C09J 7/22** (2018.01); **C09J 7/38** (2018.01); **H01L 21/304** (2006.01); **H01L 21/683** (2006.01)

CPC (source: EP KR US)

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Citation (search report)

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